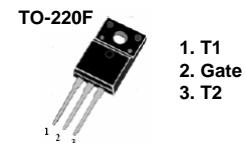
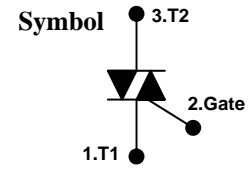


## HTS137-600 INSULATION TYPE TRIAC (TO-220F)

### FEATURES

- Repetitive Peak Off-State Voltage: 600V
- R.M.S On-state Current ( $I_{T(RMS)}=8A$ )
- High Commutation dv/dt
- Isolation Voltage ( $V_{ISO}=1500VAC$ )

$V_{DRM} = 600 V$   
 $I_{T(RMS)} = 8.0 A$



### General Description

This device is fully isolated package suitable for AC switching application, phase control application such as fan speed and temperature modulation control, lighting control and static switching relay.

### Absolute Maximum Ratings $(Ta=25^\circ C)$

Symbol	Parameter	Value	Units
$V_{DRM}$	Repetitive Peak Off-State Voltage	600	V
$I_{T(RMS)}$	R.M.S On-State Current ( $T_c = 76^\circ C$ )	8.0	A
$I_{TSM}$	Surge On-State Current (One Cycle, 50/60Hz, Peak, Non Repetitive)	70/77	A
$V_{GM}$	Peak Gate Voltage	10	V
$I_{GM}$	Peak Gate Current	2.0	A
$P_{GM}$	Peak Gate Power Dissipation	5.0	W
$V_{ISO}$	Isolation Breakdown Voltage (RMS AC 1min)	1500	V
$T_{STG}$	Storage Temperature Range	-40 to +125	°C
$T_j$	Operating Temperature	-40 to +125	°C

**Electrical Characteristics (T<sub>a</sub>=25°C)**

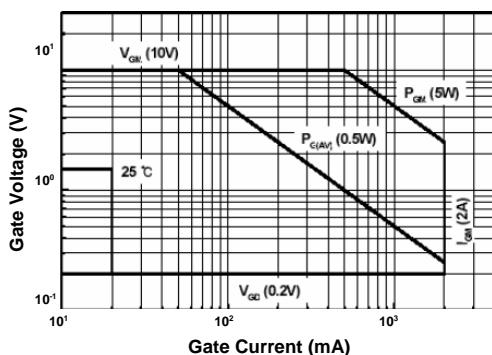
<b>Symbol</b>	<b>Parameter</b>	<b>Test Conditions</b>	<b>Min</b>	<b>Typ</b>	<b>Max</b>	<b>Units</b>
I <sub>GT</sub>	Gate Trigger Current	V <sub>D</sub> =6V, R <sub>L</sub> =10Ω			25	mA
V <sub>GT</sub>	Gate Trigger Voltage	V <sub>D</sub> =6V, R <sub>L</sub> =10Ω			1.5	V
V <sub>GD</sub>	Non Trigger Gate Voltage	T <sub>j</sub> =125°C, V <sub>D</sub> =1/2V <sub>DRM</sub>	0.2			V
(dv/dt) <sub>C</sub>	Critical Rate of Rise of Off-State Voltage at Communication	T <sub>j</sub> =125°C, V <sub>D</sub> =2/3V <sub>DRM</sub> (di/dt) <sub>C</sub> =-3A/ms	5.0			V/uS
I <sub>H</sub>	Holding Current			10.0		mA
I <sub>DRM</sub>	Repetitive Peak Off-State Current	V <sub>D</sub> =V <sub>DRM</sub> , Single Phase, Half Wave, T <sub>j</sub> =125°C			0.5	mA
V <sub>TM</sub>	Peak On-State Voltage	I <sub>T</sub> =6A, Inst, Measurement			1.6	V

**Thermal Characteristics**

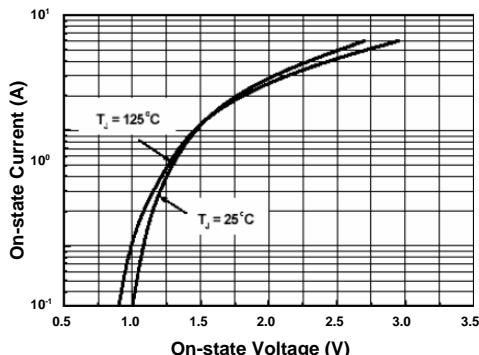
<b>Symbol</b>	<b>Parameter</b>	<b>Test Conditions</b>	<b>Min</b>	<b>Typ</b>	<b>Max</b>	<b>Units</b>
R <sub>TH(j-c)</sub>	Thermal Resistance	Junction to Case			3.8	°C/W

## Performance Curves

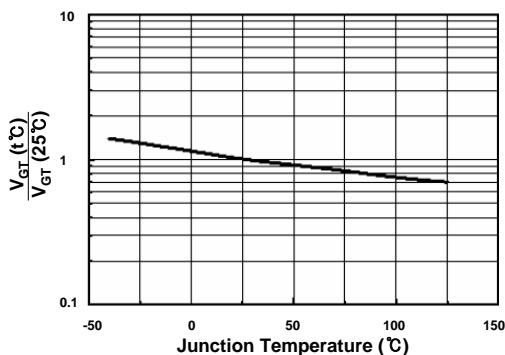
**Fig 1. Gate Characteristics**



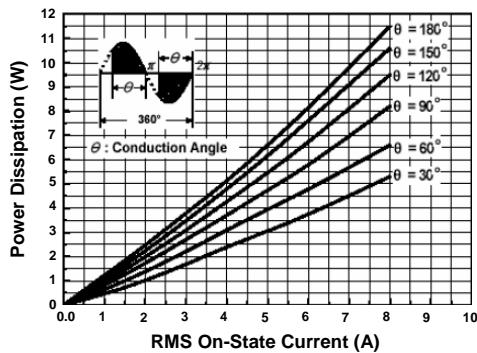
**Fig 2. On-State Voltage**



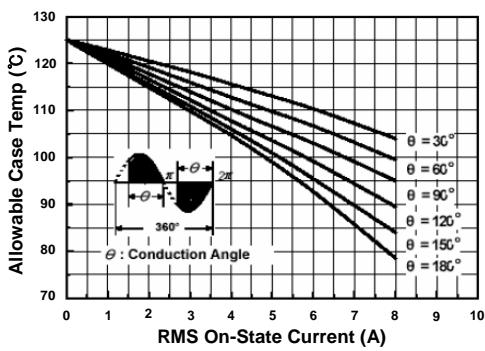
**Fig 3. Gate Trigger Voltage vs. Junction Temperature**



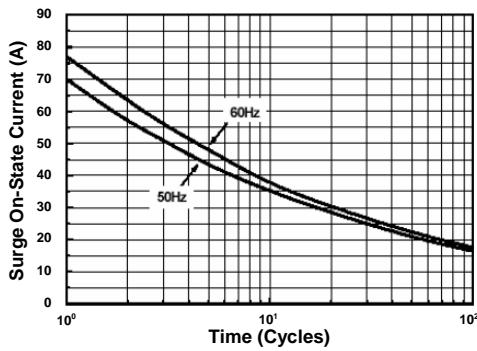
**Fig 4. On State Current vs. Maximum Power Dissipation**



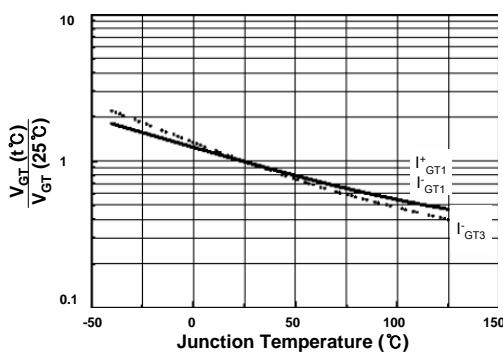
**Fig 5. On State Current vs. Allowable Case Temperature**



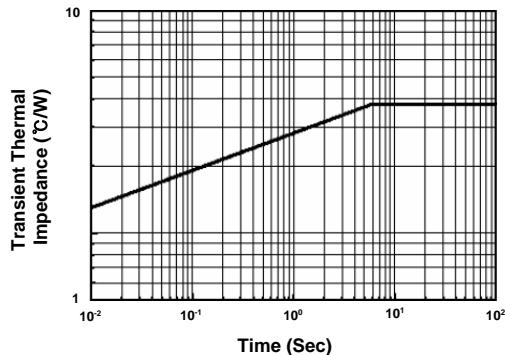
**Fig 6. Surge On-State Current Rating (Non-Repetitive)**



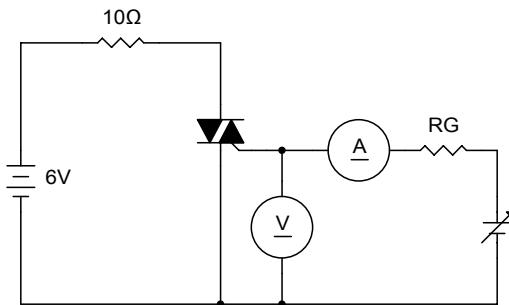
**Fig 7. Gate Trigger Current vs. Junction Temperature**



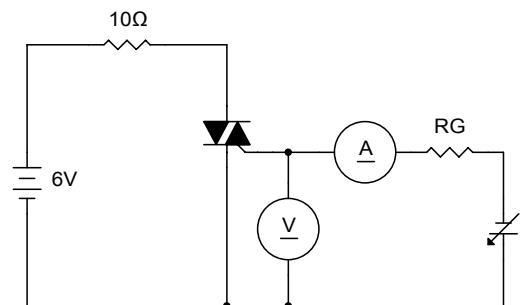
**Fig 8. Transient Thermal Impedance**



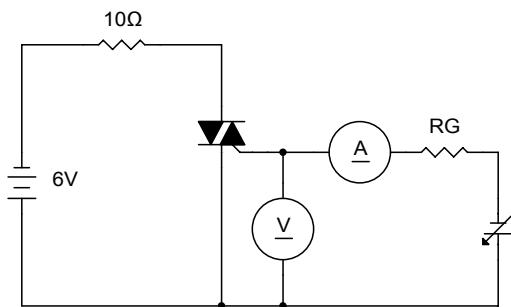
**Fig 7. Gate Trigger Characteristics Test Circuit**



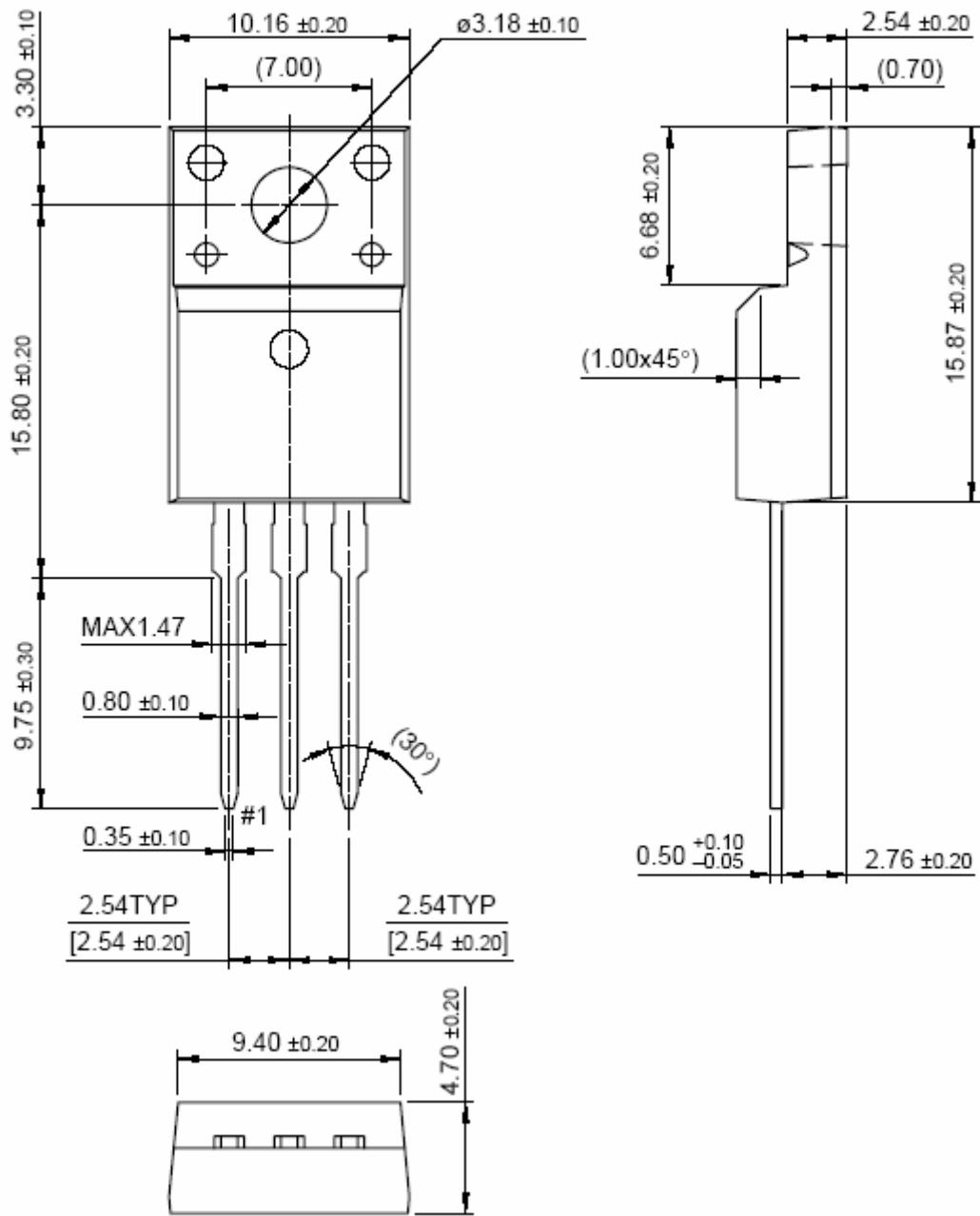
Test Procedure I



Test Procedure II



Test Procedure III

**Package Dimensions****HTS137-600  
(TO-220F)**

Dimensions in Millimeters